

Seydi DoÄan

List of Publications by Year in descending order

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Version: 2024-02-01

64
papers

11,982
citations

257450

24
h-index

149698

56
g-index

65
all docs

65
docs citations

65
times ranked

13557
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Mobile system: detecting buried objects by magnetic anomaly method. Journal of Applied Remote Sensing, 2021, 15, . | 1.3 | 2 |
| 2 | Development of a photovoltaic panel emulator and LabVIEW-based application platform. Computer Applications in Engineering Education, 2020, 28, 1291-1310. | 3.4 | 7 |
| 3 | Detection and Imaging of Underground Objects for Distinguishing Explosives by Using a Fluxgate Sensor Array. Applied Sciences (Switzerland), 2019, 9, 5415. | 2.5 | 4 |
| 4 | Design of a multi-channel quartz crystal microbalance data acquisition system. Measurement Science and Technology, 2018, 29, 075009. | 2.6 | 5 |
| 5 | Classification of explosives materials detected by magnetic anomaly method. , 2017, , . | | 1 |
| 6 | Design of a data acquisition system for passive detection of buried explosives. , 2017, , . | | 0 |
| 7 | Lutentium incorporation influence on ZnO thin films coated via a sol-gel route: spin coating technique. Journal of Materials Science: Materials in Electronics, 2016, 27, 5089-5098. | 2.2 | 2 |
| 8 | Designing a portable data acquisition system for human-computer interface applications. , 2015, , . | | 0 |
| 9 | Digital signal processing and classification study for electrooculogram signals. , 2015, , . | | 0 |
| 10 | Characteristic evaluation on spray-deposited WFTO thin films as a function of W doping ratio. Rare Metals, 2014, 33, 433-441. | 7.1 | 18 |
| 11 | Fabrication and characterization of Al ₂ Cu ₂ ZnS ₄ heterojunction photodiodes. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 580-586. | 1.8 | 31 |
| 12 | Structural characterizations and optical properties of InSe and InSe:Ag semiconductors grown by Bridgman/Stockbarger technique. Physica E: Low-Dimensional Systems and Nanostructures, 2014, 64, 106-111. | 2.7 | 39 |
| 13 | An investigation of the Nb doping effect on structural, morphological, electrical and optical properties of spray deposited F doped SnO ₂ films. Physica Scripta, 2013, 87, 035602. | 2.5 | 42 |
| 14 | W doped SnO ₂ growth via sol-gel routes and characterization: Nanocubes. Optik, 2013, 124, 4827-4831. | 2.9 | 27 |
| 15 | Growth and characterization of Ag/n-ZnO/p-Si/Al heterojunction diode by sol-gel spin technique. Journal of Alloys and Compounds, 2013, 550, 129-132. | 5.5 | 69 |
| 16 | Effect of Nb doping on structural, electrical and optical properties of spray deposited SnO ₂ thin films. Superlattices and Microstructures, 2013, 56, 107-116. | 3.1 | 98 |
| 17 | A study on characterization of Al/ZnS/p-Si/Al heterojunction diode synthesized by sol-gel technique. Materials Letters, 2013, 102-103, 106-108. | 2.6 | 26 |
| 18 | Evaluation of Structural and Optical Properties of Mn-Doped ZnO Thin Films Synthesized by Sol-Gel Technique. Metallurgical and Materials Transactions A: Physical Metallurgy and Materials Science, 2012, 43, 5088-5095. | 2.2 | 19 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | Investigation of structural and optical properties of ZnO films co-doped with fluorine and indium. Superlattices and Microstructures, 2012, 52, 107-115. | 3.1 | 77 |
| 20 | Structural and optical properties of ZnO thin films by the spin coating Sol-Gel method. Journal of Sol-Gel Science and Technology, 2011, 60, 66-70. | 2.4 | 11 |
| 21 | Capacitance and conductanceâ€“frequency characteristics of Auâ€“Sb/p-GaSe:Gd Schottky barrier diode. Vacuum, 2011, 85, 798-801. | 3.5 | 26 |
| 22 | Electrical characterization of Ag/p-GaSe:Gd schottky barrier diodes. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 1958-1962. | 2.7 | 12 |
| 23 | InAlN/GaN heterostructure field-effect transistors on Fe-doped semi-insulating GaN substrates. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, 908-911. | 1.2 | 7 |
| 24 | Photoionization study of deep centers in GaNâ€“AlGaIn multiple quantum wells. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, C3110-C3112. | 1.2 | 0 |
| 25 | Temperature-dependent electrical characterization of nitrogen-doped ZnO thin film: vacuum annealing effect. Physica Scripta, 2009, 79, 035701. | 2.5 | 7 |
| 26 | Electrical characteristics and inhomogeneous barrier analysis of Auâ€“Be/p-InSe:Cd Schottky barrier diodes. Microelectronic Engineering, 2009, 86, 106-110. | 2.4 | 10 |
| 27 | Temperature variation of currentâ€“voltage characteristics of Au/Ni/n-GaN Schottky diodes. Physica E: Low-Dimensional Systems and Nanostructures, 2009, 41, 646-651. | 2.7 | 53 |
| 28 | Temperature dependent capacitance and DLTS studies of Ni/n-type 6H-SiC Schottky diode. Current Applied Physics, 2009, 9, 1181-1185. | 2.4 | 10 |
| 29 | Urbach tail and electric field influence on optical properties of InSe and InSe:Er single crystals. Applied Physics A: Materials Science and Processing, 2008, 90, 479-485. | 2.3 | 11 |
| 30 | The barrier-height inhomogeneity in identically prepared Ni/n-type 6H-SiC Schottky diodes. Applied Physics A: Materials Science and Processing, 2008, 91, 337-340. | 2.3 | 26 |
| 31 | The effects of the temperature and annealing on currentâ€“voltage characteristics of Ni/n-type 6Hâ€“SiC Schottky diode. Microelectronic Engineering, 2008, 85, 631-635. | 2.4 | 31 |
| 32 | Direct recognition of non-radiative recombination centers in semi-insulating LEC InP:Fe using double excitation photoluminescence. Journal of Luminescence, 2008, 128, 232-238. | 3.1 | 8 |
| 33 | Determination of the transport mechanisms in mixed conduction of reactively sputtered ZnO thin films. Journal Physics D: Applied Physics, 2008, 41, 135309. | 2.8 | 2 |
| 34 | Observation of surface charging at the edge of a Schottky contact. IEEE Electron Device Letters, 2006, 27, 211-213. | 3.9 | 14 |
| 35 | Comparison of deep levels in GaN grown by MBE, MOCVD, and HVPE. , 2005, , . | | 13 |
| 36 | High efficiency n-ZnO/p-SiC heterostructure photodiodes grown by plasma-assisted molecular-beam epitaxy. Superlattices and Microstructures, 2005, 38, 439-445. | 3.1 | 22 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 37 | Forward-current electroluminescence from GaN/ZnO double heterostructure diode. Solid-State Electronics, 2005, 49, 1693-1696. | 1.4 | 24 |
| 38 | A comprehensive review of ZnO materials and devices. Journal of Applied Physics, 2005, 98, 041301. | 2.5 | 9,857 |
| 39 | Characterization of MOCVD grown GaN on porous SiC templates. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2087-2090. | 0.8 | 7 |
| 40 | Deep levels in KOH etched and MOCVD regrown GaN p-n junctions. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2454-2457. | 0.8 | 0 |
| 41 | A study of GaN regrowth on the micro-faceted GaN template formed by in-situ thermal etching. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 718-721. | 1.8 | 15 |
| 42 | Reduction of threading dislocations in GaN overgrowth by MOCVD on TiN porous network templates. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 749-753. | 1.8 | 5 |
| 43 | Surface charging and current collapse in an AlGaIn/GaN heterostructure field effect transistor. Applied Physics Letters, 2005, 86, 083506. | 3.3 | 21 |
| 44 | Effectiveness of TiN porous templates on the reduction of threading dislocations in GaN overgrowth by organometallic vapor-phase epitaxy. Applied Physics Letters, 2005, 86, 043108. | 3.3 | 55 |
| 45 | Effect of n+-GaIn subcontact layer on 4H-SiC high-power photoconductive switch. Applied Physics Letters, 2005, 86, 261108. | 3.3 | 27 |
| 46 | Photoresponse of n-ZnO/p-SiC heterojunction diodes grown by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 241108. | 3.3 | 140 |
| 47 | Effects of hydrostatic and uniaxial stress on the Schottky barrier heights of Ga-polarity and N-polarity n-GaN. Applied Physics Letters, 2004, 84, 2112-2114. | 3.3 | 45 |
| 48 | Investigation of forward and reverse current conduction in GaN films by conductive atomic force microscopy. Applied Physics Letters, 2004, 84, 4150-4152. | 3.3 | 56 |
| 49 | Determination of the carrier concentration in InGaAs/GaAs single quantum wells using Raman scattering. Applied Physics Letters, 2004, 85, 4905-4907. | 3.3 | 8 |
| 50 | Thermal stability of electron traps in GaN grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2004, 85, 4058-4060. | 3.3 | 15 |
| 51 | Surface band bending in as-grown and plasma-treated n-type GaN films using surface potential electric force microscopy. Applied Physics Letters, 2004, 84, 3070-3072. | 3.3 | 42 |
| 52 | The effect of hydrogen etching on 6H-SiC studied by temperature-dependent current-voltage and atomic force microscopy. Applied Physics Letters, 2004, 85, 1547-1549. | 3.3 | 38 |
| 53 | Excitonic fine structure and recombination dynamics in single-crystalline ZnO. Physical Review B, 2004, 70, . | 3.2 | 662 |
| 54 | p-GaN-i-GaN/AlGaIn multiple-quantum well n-AlGaIn back-illuminated ultraviolet detectors. Journal of Electronic Materials, 2003, 32, 307-311. | 2.2 | 7 |

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|----|--|-----|-----------|
| 55 | GaN/AlGaIn back-illuminated multiple-quantum-well Schottky barrier ultraviolet photodetectors. Solid-State Electronics, 2003, 47, 1401-1408. | 1.4 | 24 |
| 56 | Electric field influence on absorption measurement in InSe single crystal. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 274-279. | 2.7 | 20 |
| 57 | Convertibility of conductivity type in reactively sputtered ZnO thin films. Physica Status Solidi A, 2003, 195, 165-170. | 1.7 | 16 |
| 58 | 4H α -SiC photoconductive switching devices for use in high-power applications. Applied Physics Letters, 2003, 82, 3107-3109. | 3.3 | 93 |
| 59 | Improvement of n-GaN Schottky diode rectifying characteristics using KOH etching. Applied Physics Letters, 2003, 82, 3556-3558. | 3.3 | 31 |
| 60 | Temperature Dependence of Magnetoresistance and Hall Effect for Ho Doped n-Type InSe. Physica Scripta, 2000, 62, 92-96. | 2.5 | 4 |
| 61 | In situ optical assessment of semi-insulating iron doped InP grown by liquid encapsulated Czochralski process. Journal of Applied Physics, 1999, 85, 6777-6781. | 2.5 | 8 |
| 62 | Growth and Temperature Dependence of Optical Properties of Er Doped and Undoped n-Type InSe. Japanese Journal of Applied Physics, 1999, 38, 5133-5136. | 1.5 | 25 |
| 63 | Anomalous Behaviour of Galvanomagnetic Effects in Very Lightly n-Type Bulk GaAs: Possible Role of Reverse-Contrast Centres. Physica Status Solidi A, 1999, 174, 467-475. | 1.7 | 4 |
| 64 | Current conduction mechanisms of heteroepitaxial and homoepitaxial GaN films grown by MBE. , 0, , . | | 0 |